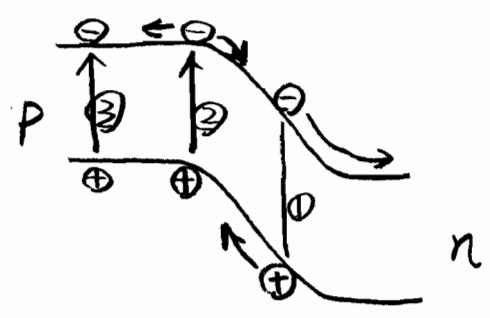


P-i-n Photodiode

Reverse-biased p-n junction.

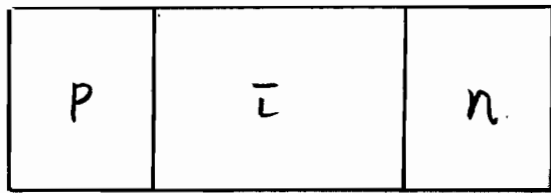


Photon absorbed in

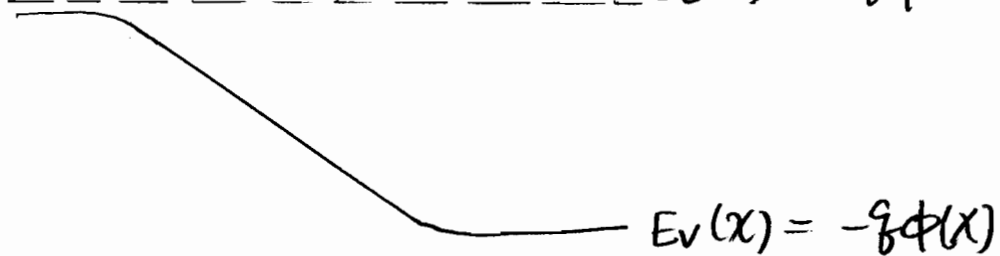
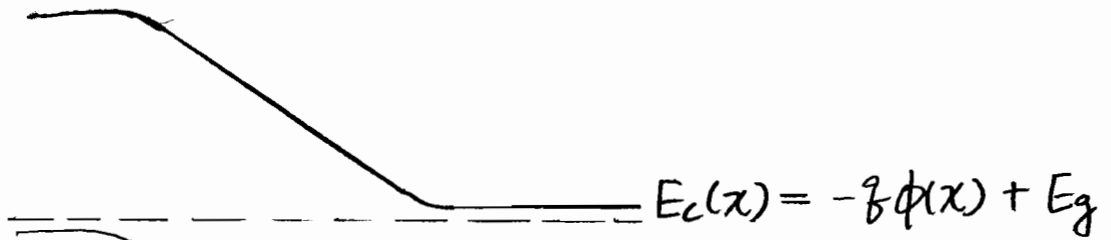
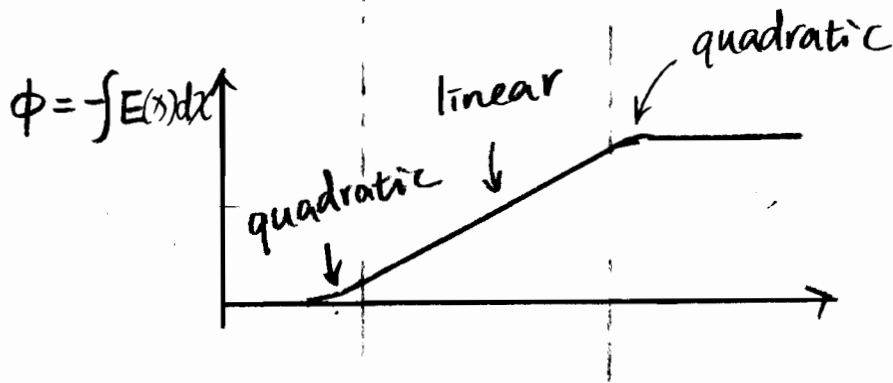
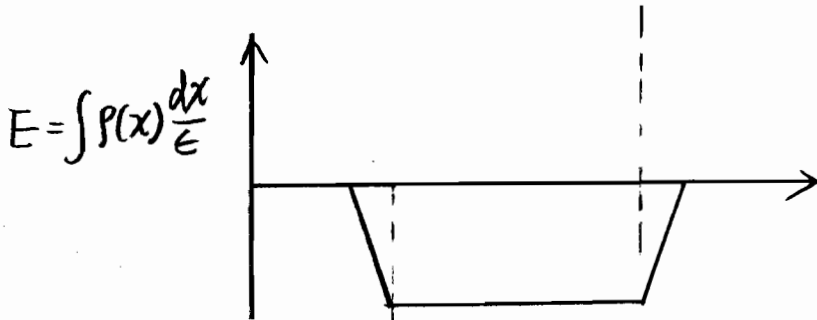
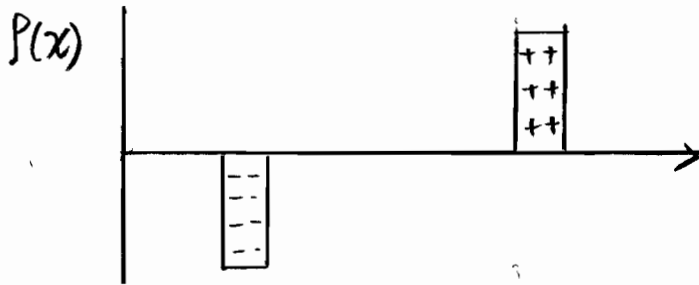
- ① depletion region. electrons and holes are separated and collected
- ② depletion (e.g. on p-side): electron will diffuse to depletion region, and produce photocurrent
- ③ neutral region: recombine without generating i_{ph}

- ① most desirable
- ② may have long tail in temporal response (diffusion tail)

To widen depletion region. \Rightarrow P-i-n.



P and n region
can be large- E_g
material to
minimize absorption
 \Rightarrow P-i-N

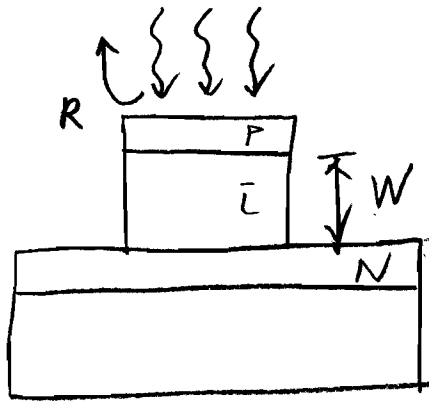


Additional benefits of P-I-N

- Smaller capacitance \Rightarrow smaller RC, higher speed
- Longer absorption \Rightarrow higher efficiency
- But longer transit time \Rightarrow lower speed.

Quantum Efficiency

① Surface-illuminated P-I-N



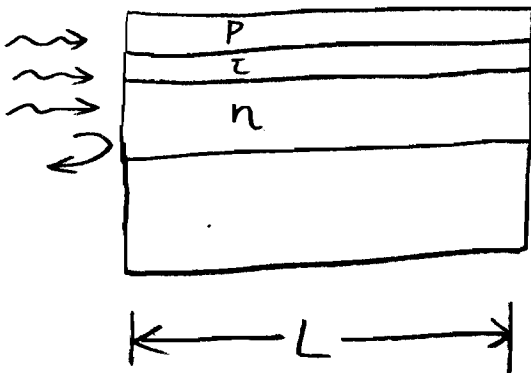
Neglect diffusion current

$$\eta = \eta_i (1-R) (1 - e^{-\alpha W})$$

α = absorption coef

$\alpha \sim 10^4 \text{ cm}^{-1}$ for direct bandgap

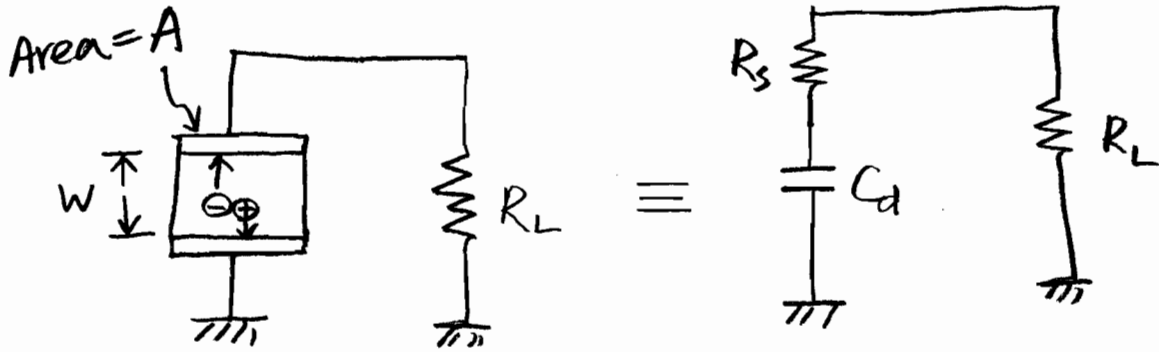
② Waveguide P-I-N



$$\eta = \eta_i (1-R) (1 - e^{-\alpha P L})$$

P = confinement factor

Frequency Response



① RC charging

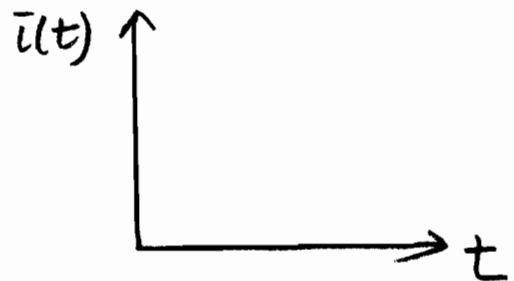
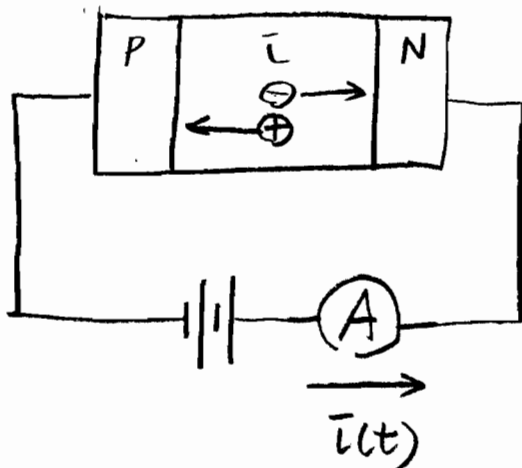
② Transit time

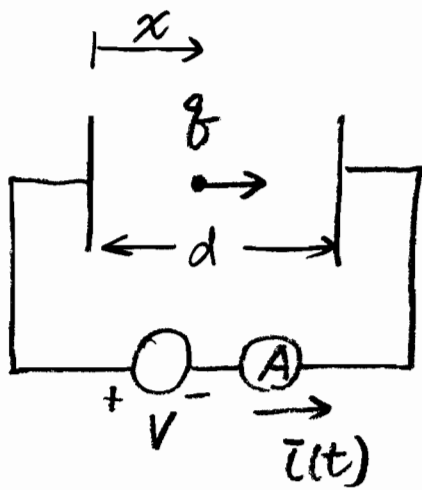
RC: $R = R_s + R_L$ ← input impedance of the following stage
 ↑
 contact resistance
 + resistance of P and N region.

$$C_d = \frac{\epsilon A}{W}$$

$$WRC = \frac{1}{RC_d}$$

Transit time:





Current caused in the external circuit by a moving charge q in a parallel plate capacitor with a separation of d and voltage bias of V :

$$i(t) = \frac{q V(t)}{d}$$

Proof: work done on the charge

$$W = \text{Force} \cdot \text{distance} = q \cdot E \cdot dx = q \frac{V}{d} \cdot dx$$

work provided by power supply

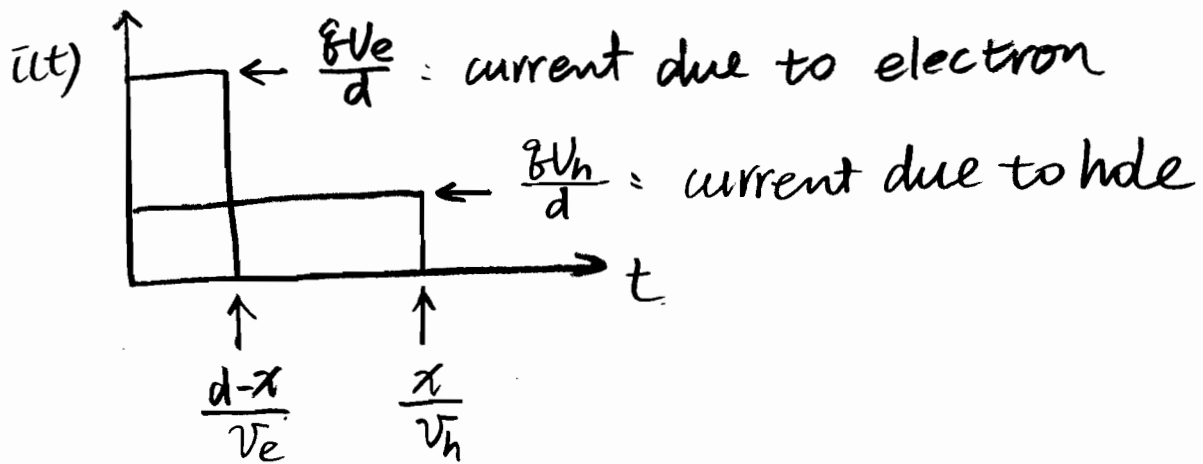
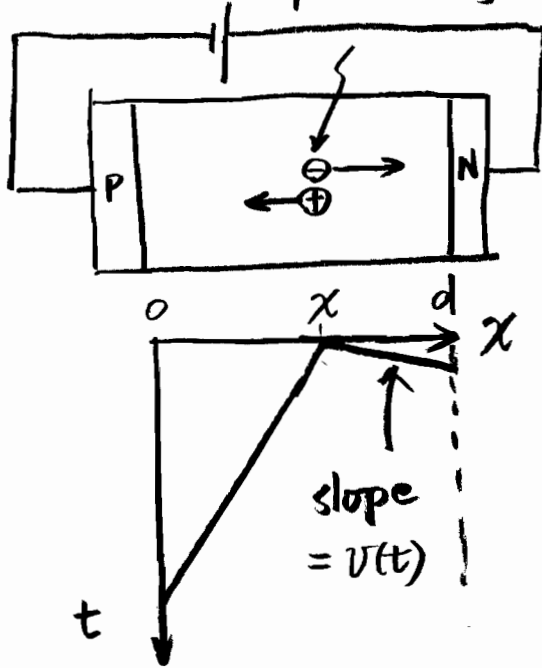
$$W = V \cdot i(t) \cdot dt$$

$$\Rightarrow V \cdot i(t) dt = V \cdot \frac{q}{d} dx$$

$$\Rightarrow i(t) = \frac{q}{d} \frac{dx}{dt} = \frac{q V(t)}{d} \quad \#$$

Transit Time Concept

* Due to absorption of a single photon



Area = total charge induced in external circuit

$$\frac{qV_e}{d} \cdot \frac{d-x}{v_e} + \frac{qV_h}{d} \cdot \frac{x}{v_h} = q \left(\frac{d-x}{d} + \frac{x}{d} \right) = q$$

* Simple estimation of transit time

$$\frac{d}{v_h} \quad (\text{hole is usually slower})$$

* Small-signal approach.

Incident optical field

$$E = E_s (1 + m \cdot \cos \omega_m t) \cdot \cos \omega t$$

\uparrow modulating freq \uparrow optical freq.

$$= \text{Re} [V(t)]$$

$$V(t) = E_s (1 + m \cos \omega_m t) \cdot e^{i\omega t}$$

Generation rate

$$G(t) = a \left\langle \frac{1}{2} V(t) V^*(t) \right\rangle$$

\uparrow time average

$$= a E_s^2 \left[1 + \frac{m^2}{2} + 2m e^{i\omega_m t} \right]$$

$$\bar{i}(t) = \frac{e\bar{v}}{d} \quad \tau_d = \frac{d}{v} : \text{transit time}$$

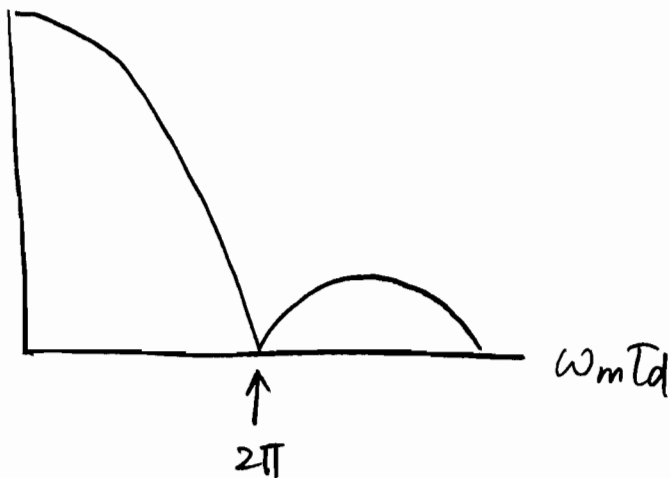
$$\bar{i}(t) = \frac{e\bar{v}}{d} \int_{t-\tau_d}^t G(t') dt'$$

$$= \left(1 + \frac{m^2}{2}\right) e \cdot a \cdot E_s^2 + 2m \cdot e \cdot a \cdot E_s^2 \cdot \left(\frac{1 - e^{-i\omega_m \tau_d}}{i\omega_m \tau_d} \right) e^{i\omega_m t}$$

Setting $m=0$ $\bar{I} = \frac{P_e \eta}{h\nu} = e \cdot a \cdot E_s^2$

$$\bar{i}(t) = \frac{P_e \eta}{h\nu} \left[\left(1 + \frac{m^2}{2}\right) + 2m \cdot \left(\frac{1 - e^{-i\omega_m \tau_d}}{i\omega_m \tau_d} \right) e^{i\omega_m t} \right]$$

$$|i(t)_{ac}| \propto \left| \frac{1 - e^{-i\omega_m t_d}}{i\omega_m t_d} \right| = \frac{\sin\left(\frac{\omega_m t_d}{2}\right)}{\left(\frac{\omega_m t_d}{2}\right)}$$



3-dB point ($\frac{1}{\sqrt{2}}$)

$$\frac{\omega_m t_d}{2} \approx 1.04$$

$$2\pi f_m t_d \approx 2.8$$

$$f_m = \frac{2.8}{2\pi} \cdot \frac{1}{t_d} \approx 0.44 \frac{1}{t_d}$$

$\frac{1}{e}$ point

$$\frac{\omega_m t_d}{2} \approx 2.2$$

$$f_m \approx \frac{4.4}{2\pi} \frac{1}{t_d}$$

Total response time

$$T = T_{rc} + T_t = RC + \frac{1}{4.4} t_d$$

$$f = \frac{1}{2\pi T}$$

Example

p-i-n . $10\mu\text{m} \times 10\mu\text{m}$,

$$R = 50\Omega$$

$$RC = \frac{REA}{d} = \frac{10^{-12} \cdot 10^2 \times 10^{-8}}{d} \times 50$$

$$\tau_t = \frac{1}{4.4} \cdot \frac{d}{v_n}$$

$$RC + \tau_t \geq 2 \sqrt{\frac{\epsilon A R d}{d \cdot 4.4 v_n}} = 2 \sqrt{\frac{\epsilon A R}{4.4 v_n}}$$

Max freq achieved (min τ) when

$$RC = \tau_t$$

$$\text{or } d = \sqrt{4.4 v_n \cdot \epsilon A \cdot R} \leftarrow 50\Omega$$

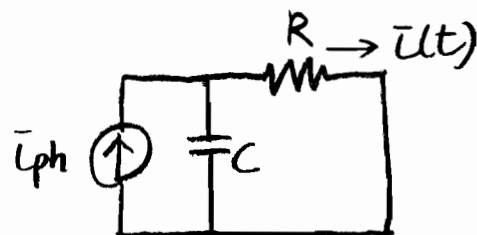
$\uparrow \quad \nwarrow \quad \swarrow$
 $5 \times 10^6 \text{ cm/sec} \quad 10^{-12} \text{ F/cm} \quad 10^{-6} \text{ cm}^2$

$$d \approx 0.3\mu\text{m}$$

* More rigorous analysis

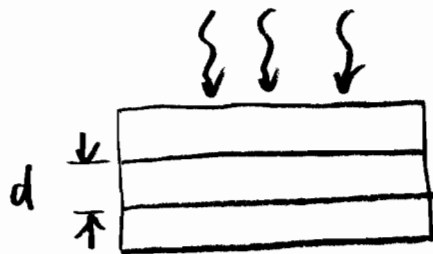
$$|\bar{u}(t)| \propto \left| \frac{\frac{1}{i\omega C}}{R + \frac{1}{i\omega C}} \right| \cdot \text{sinc}\left(\frac{\omega m T d}{2}\right)$$

$$= \left| \frac{1}{1 + i\omega RC} \right| \cdot \text{sinc}\left(\frac{\omega m T d}{2}\right)$$



Equivalent circuit

Efficiency Consideration



Surface-illuminated P-i-n

$$\eta = \eta_i (1 - e^{-\alpha d})$$

There is a quantum efficiency - bandwidth trade-off

* High $\eta \rightarrow$ large $d \rightarrow$ long transit time
 \rightarrow low bandwidth

* Simplified case, assume

- Low efficiency $\eta(d) \approx \eta_i (1 - 1 + \alpha d) = \eta_i \alpha d$

- Transit time limited BW

$$f_{3dB} \approx 0.44 \frac{v_h}{d}$$

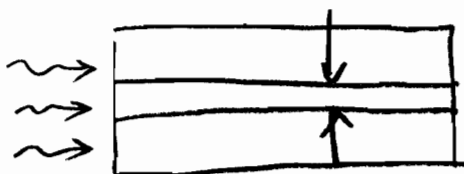
$$\eta \times f_{3dB} \approx \eta_i \alpha d \times 0.44 \frac{v_h}{d} \approx 0.44 \eta_i \alpha \cdot v_h$$

$$\alpha \sim 10^4 \text{ cm}^{-1}$$

$$v_h \sim 5 \times 10^6 \text{ cm/sec}$$

$$\eta_i \sim 100\%$$

$$\eta \times f_{3dB} \approx 2.2 \times 10^{10}$$



Waveguide PD (edge-illuminated)

does not have $\eta - f_{3dB}$ trade-off